

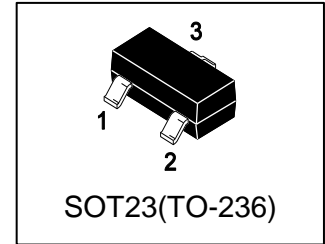
LMBT3906LT1G

S-LMBT3906LT1G

General Purpose Transistors PNP Silicon

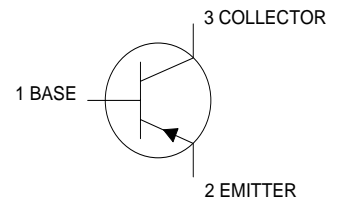
1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.



2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LMBT3906LT1G	2A	3000/Tape&Reel
LMBT3906LT3G	2A	10000/Tape&Reel



3. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector–Emitter Voltage	V _{CEO}	-40	V
Collector–Base Voltage	V _{CBO}	-40	V
Emitter–Base Voltage	V _{EBO}	-5	V
Collector Current — Continuous	I _C	-200	mA

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-5 Board (Note 1) @ TA = 25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction–to–Ambient(Note 1)	R _{θJA}	556	°C/W
Junction and Storage temperature	T _J , T _{stg}	-55~+150	°C

1. FR-5 = 1.0×0.75×0.062 in.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Collector–Emitter Breakdown Voltage (IC = -1.0 mA, IB = 0)	VBR(CEO)	-40	-	-	V
Collector–Base Breakdown Voltage (IC = -10 μA, IE = 0)	VBR(CBO)	-40	-	-	V
Emitter–Base Breakdown Voltage (IE = -10 μA, IC = 0)	VBR(EBO)	-5	-	-	V
Collector Cutoff Current (VCE = -30 V, VEB = -3.0V)	ICEX	-	-	-50	nA
Base Cutoff Current (VCE = -30 V, VEB = -3.0V)	IBL	-	-	-50	nA

ON CHARACTERISTICS (Note 2.)

DC Current Gain (IC = -0.1 mA, VCE = -1.0 V)	HFE	60	-	-	
(IC = -1.0 mA, VCE = -1.0 V)		80	-	-	
(IC = -10 mA, VCE = -1.0 V)		100	-	300	
(IC = -50 mA, VCE = -1.0 V)		60	-	-	
(IC = -100 mA, VCE = -1.0 V)		30	-	-	
Collector–Emitter Saturation Voltage (IC = -10 mA, IB = -1.0 mA)	VCE(sat)	-	-	-0.25	V
(IC = -50 mA, IB = -5.0 mA)		-	-	-0.4	
Base–Emitter Saturation Voltage (IC = -10 mA, IB = -1.0 mA)	VBE(sat)	-0.65	-	-0.85	V
(IC = -50 mA, IB = -5.0 mA)		-	-	-0.95	

SMALL–SIGNAL CHARACTERISTICS

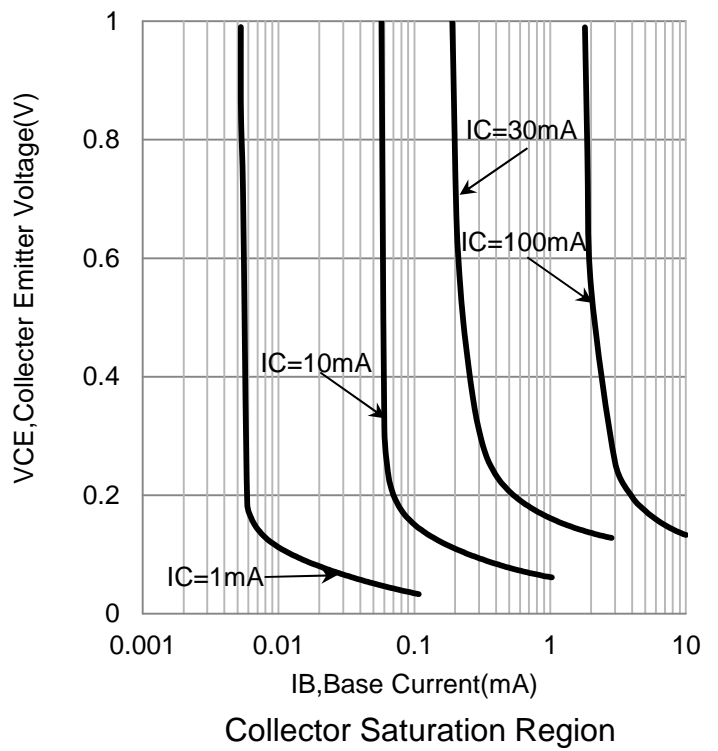
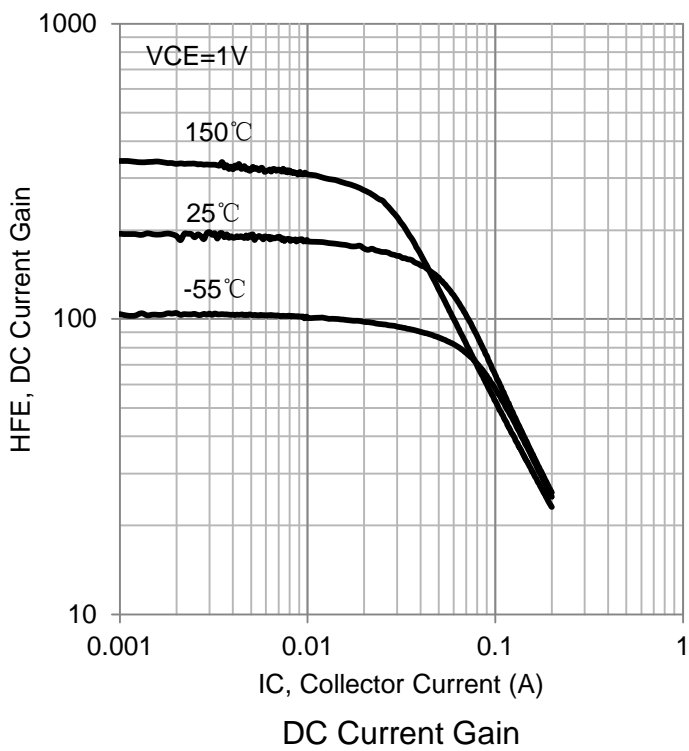
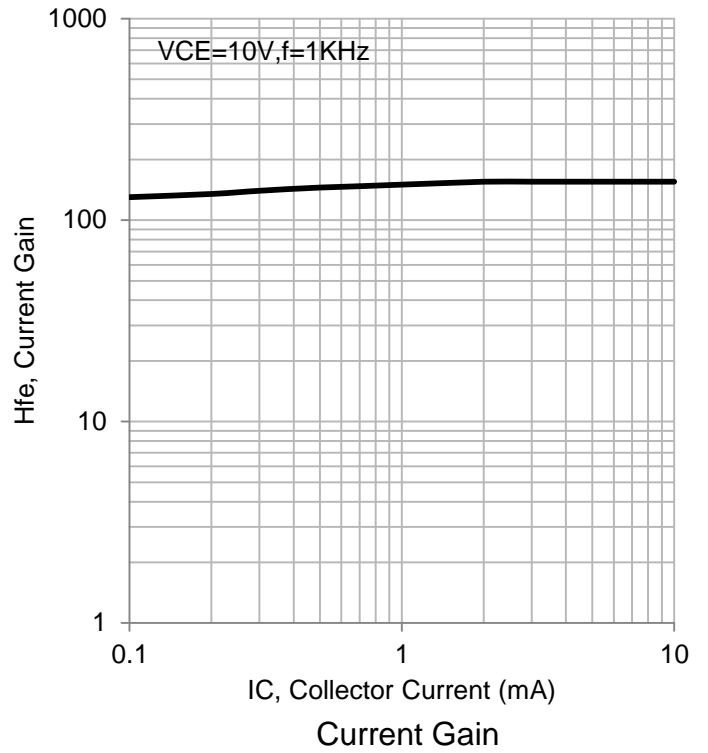
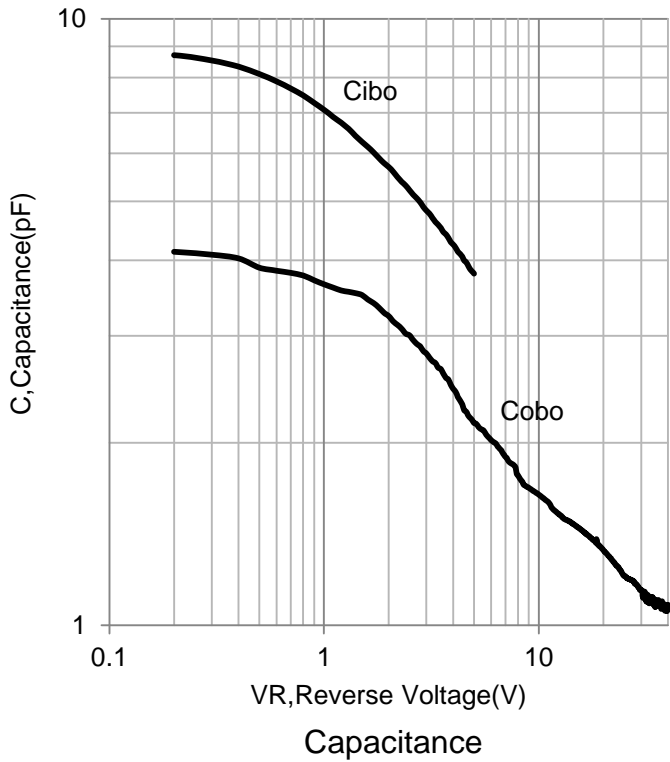
Current–Gain — Bandwidth Product (IC = -10mA, VCE= -20V, f = 100MHz)	fT	250	-	-	MHz
Output Capacitance (VCB = -5.0 V, IE = 0, f = 1.0 MHz)	Cobo	-	-	4.5	pF
Input Capacitance (VEB = -0.5 V, IC = 0, f = 1.0 MHz)	Cibo	-	-	10	pF

SWITCHING CHARACTERISTICS

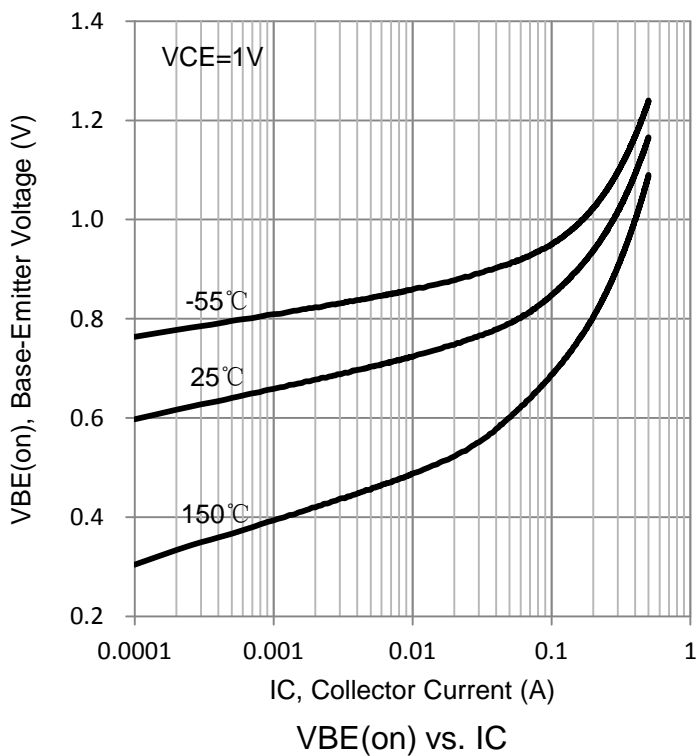
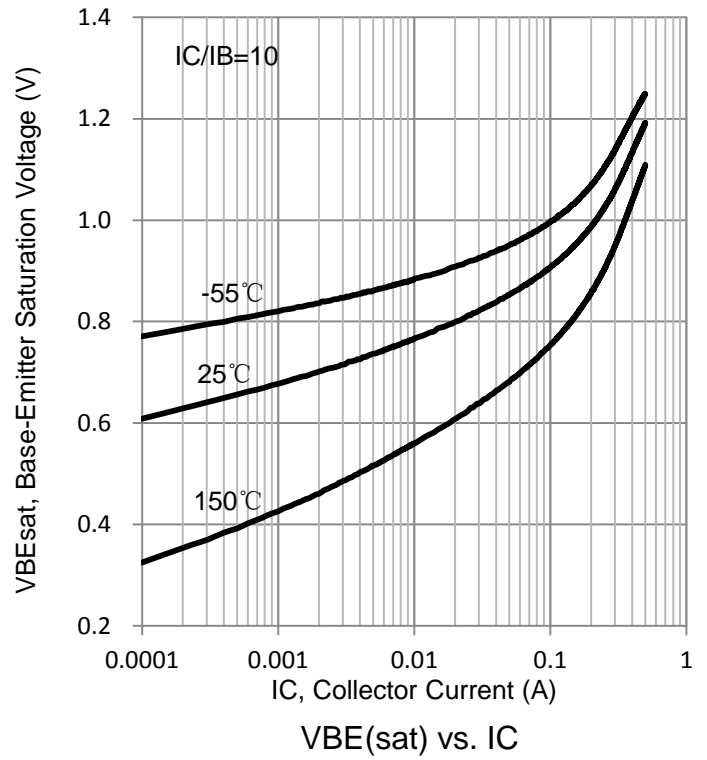
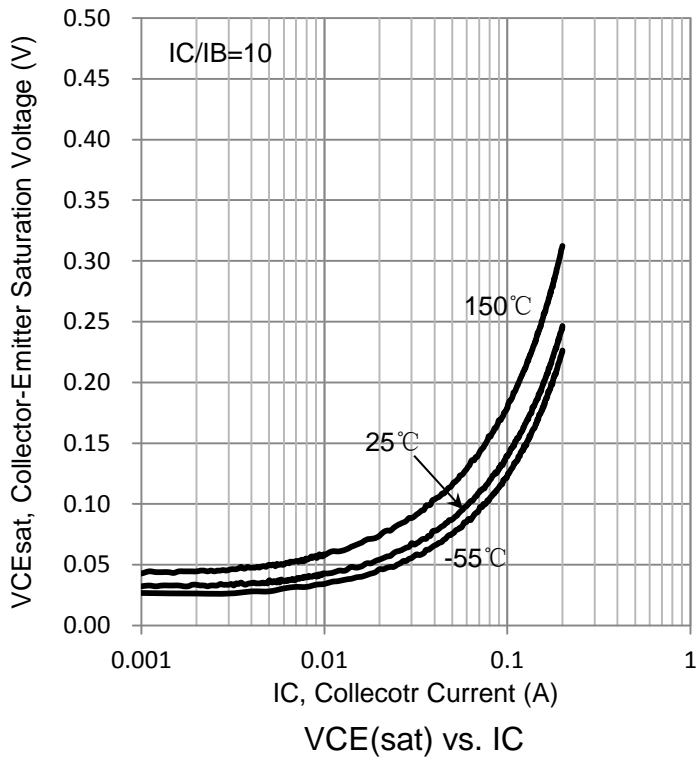
Delay Time	(VCC = -3.0 V, VBE=0.5V, IC = -10mA, IB1 = -1.0 mA)	td	-	-	35	ns
Rise Time		tr	-	-	35	
Storage Time		ts	-	-	225	
Fall Time		tf	-	-	75	

 2.Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2.0\%$.

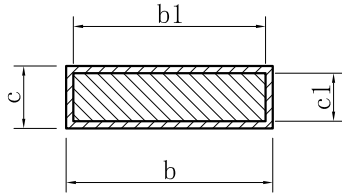
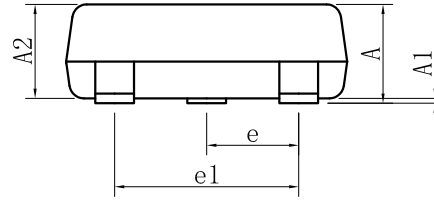
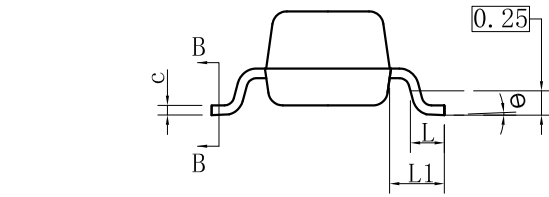
6. ELECTRICAL CHARACTERISTICS CURVES



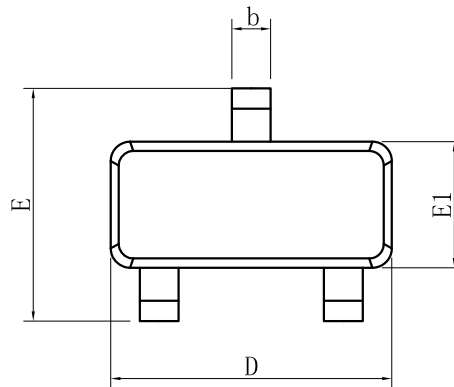
6. ELECTRICAL CHARACTERISTICS CURVES(Con.)



7. OUTLINE AND DIMENSIONS



SECTION B-B

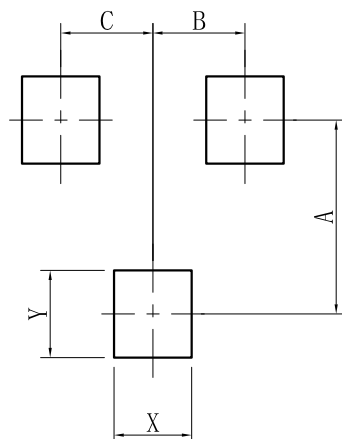


SOT23			
DIM	MIN	NOR	MAX
A	0.89	-	1.12
A1	0.01	-	0.10
A2	0.88	0.95	1.02
b	0.30	-	0.50
b1	0.30	0.40	0.45
c	0.08	-	0.20
c1	0.08	0.10	0.16
D	2.80	2.90	3.04
E	2.10	-	2.64
E1	1.20	1.30	1.40
e	0.95BSC		
e1	1.90BSC		
L	0.40	0.46	0.60
L1	0.54REF		
θ	0°	-	8°
All Dimensions in mm			

GENERAL NOTES

1. Top package surface finish Ra0.4±0.2um
2. Bottom package surface finish Ra0.7±0.2um
3. Side package surface finish Ra0.4±0.2um

8. SOLDERING FOOTPRINT



SOT-23	
DIM	(mm)
X	0.80
Y	0.90
A	2.00
B	0.95
C	0.95

DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee. The curve of test items without electric parameter is used as reference only.
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